



## N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A)	Q <sub>g</sub> (TYP.)
30	0.560 at V <sub>GS</sub> = 4.5 V	0.5	0.72 nC
	0.620 at V <sub>GS</sub> = 2.5 V	0.2	
	0.700 at V <sub>GS</sub> = 1.8 V	0.2	
	1.100 at V <sub>GS</sub> = 1.5 V	0.05	

### FEATURES

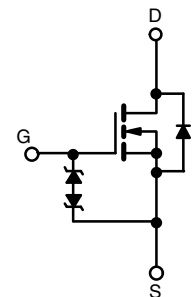
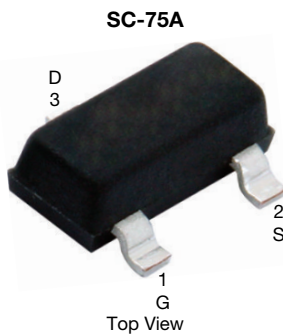
- TrenchFET® power MOSFET
- 100 % R<sub>g</sub> tested
- Gate-source ESD protected: 1000 V
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Load switch
- High speed switching
- DC/DC converters / boost converters
- For smart phones, tablet PCs and mobile computing



N-Channel MOSFET

Marking Code: L

#### Ordering Information:

Si1002R-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	± 8	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	0.61 <sup>a,b</sup>	A
	T <sub>A</sub> = 70 °C	0.49 <sup>a,b</sup>	
Pulsed Drain Current (t = 100 μs)	I <sub>DM</sub>	2	
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	0.18 <sup>a,b</sup>	A
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	0.22 <sup>a,b</sup>	W
	T <sub>A</sub> = 70 °C	0.14 <sup>a,b</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient <sup>b</sup>	R <sub>thJA</sub>	t ≤ 5 s	470	565
		Steady State	560	675

#### Notes

- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	29	-	mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>		-	-1.8	-	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.4	-	1	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 8 V	-	-	± 30	μA
		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 4.5 V	-	-	± 1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	-	-	1	
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C	-	-	3	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = ≥ 5 V, V <sub>GS</sub> = 4.5 V	2	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.5 A	-	0.450	0.560	Ω
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 0.2 A	-	0.500	0.620	
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 0.2 A	-	0.560	0.700	
		V <sub>GS</sub> = 1.5 V, I <sub>D</sub> = 0.05 A	-	0.647	1.100	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 0.5 A	-	7.5	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	36	-	pF
Output Capacitance	C <sub>oss</sub>		-	9	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	5	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 8 V, I <sub>D</sub> = 0.5 A	-	1.2	2	nC
			V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.5 A	-	0.72	
Gate-Source Charge	Q <sub>gs</sub>	-		0.1	-	
Gate-Drain Charge	Q <sub>gd</sub>	-		0.16	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	2.4	12.2	24.4	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 37.5 Ω I <sub>D</sub> = 0.4 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	-	6	15	ns
Rise Time	t <sub>r</sub>		-	13	24	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	20	30	
Fall Time	t <sub>f</sub>		-	11	20	
<b>Drain-Source Body Diode Characteristics</b>						
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>		-	-	2	A
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.5 A	-	0.8	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 0.4 A, di/dt = 100 A/μs	-	8	15	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	2	4	nC
Reverse Recovery Fall Time	t <sub>a</sub>		-	4	-	ns
Reverse Recovery Rise Time	t <sub>b</sub>		-	4	-	

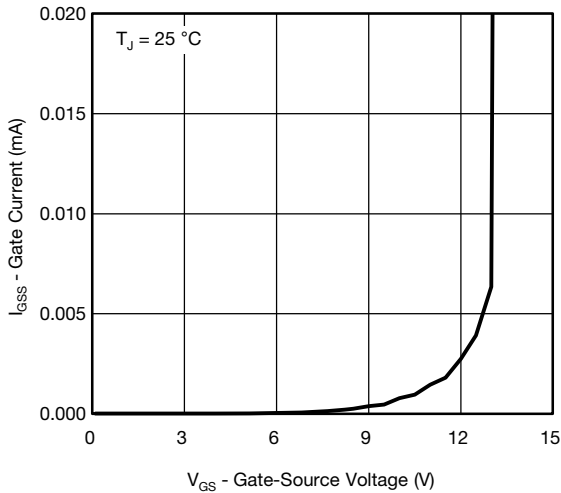
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

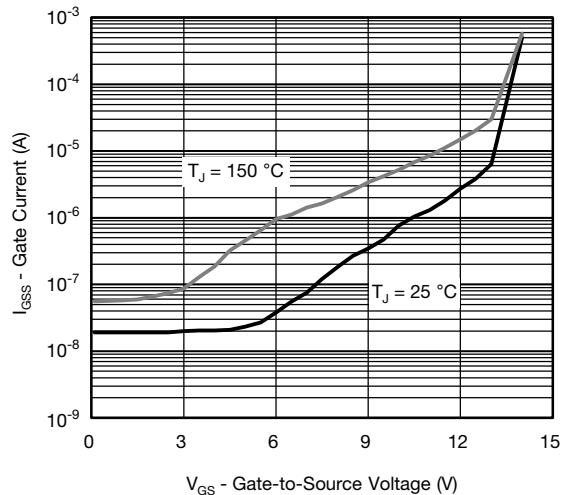
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



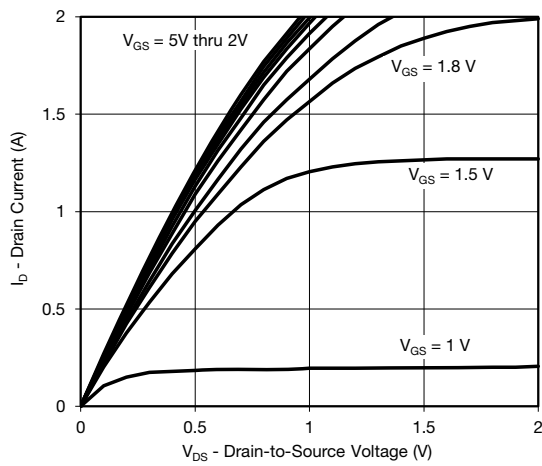
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



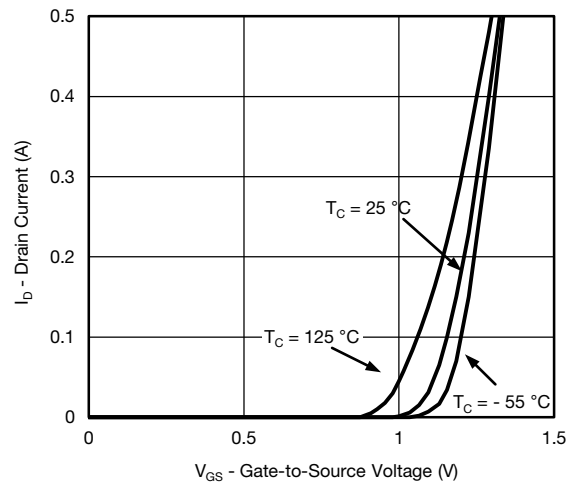
Gate Current vs. Gate-Source Voltage



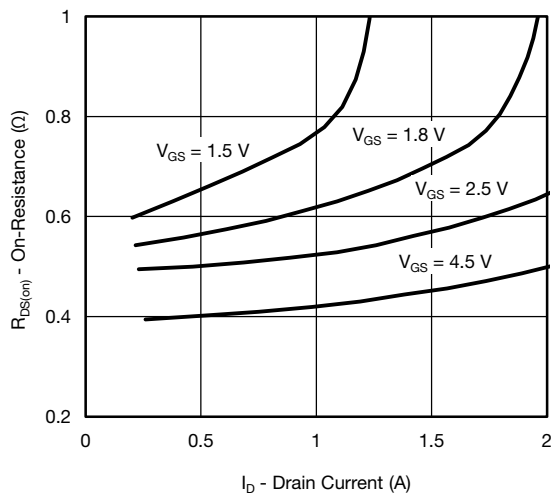
Gate Current vs. Gate-Source Voltage



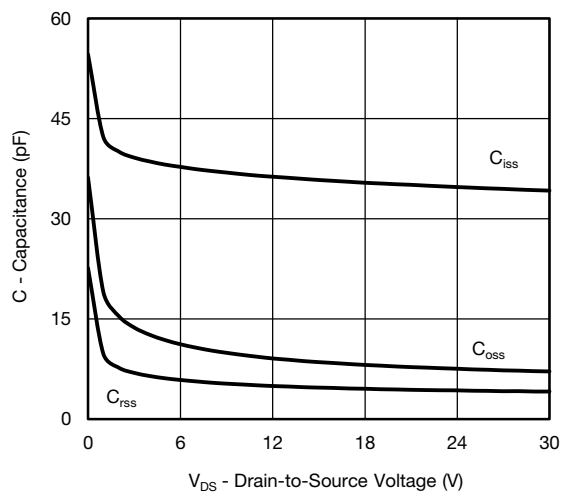
Output Characteristics



Transfer Characteristics



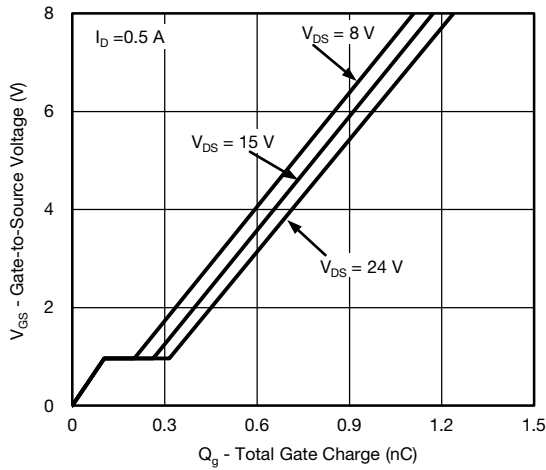
On-Resistance vs. Drain Current



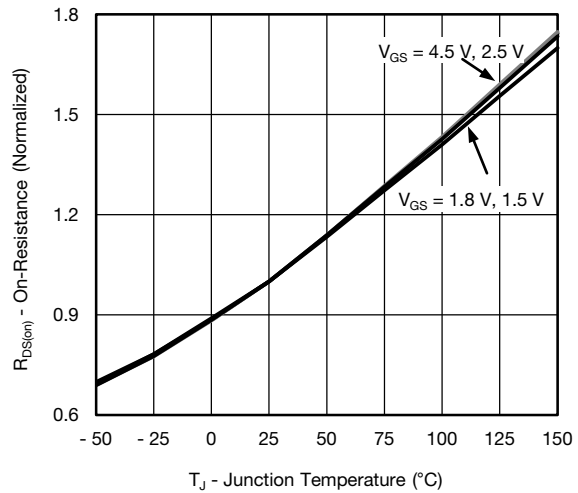
Capacitance



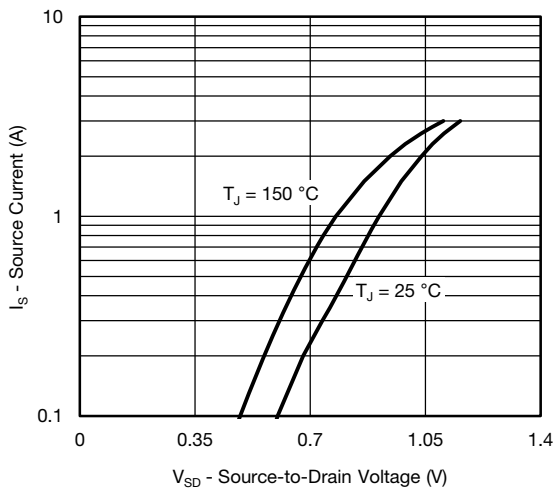
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



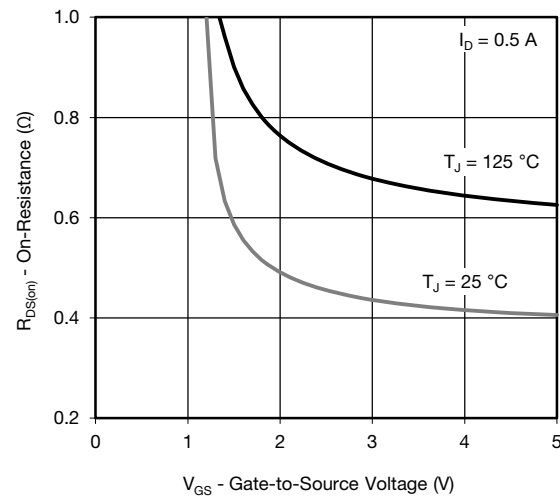
**Gate Charge**



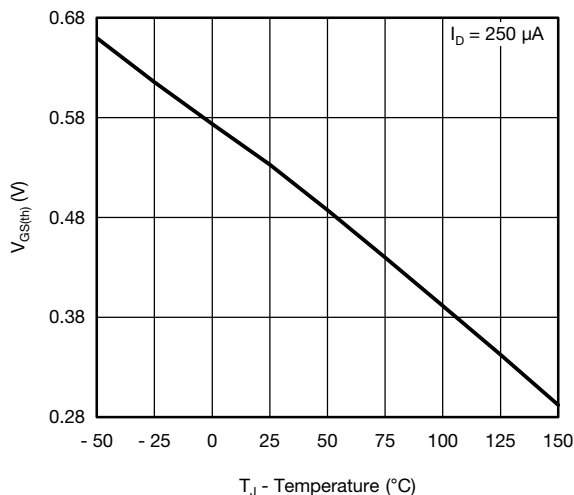
**On-Resistance vs. Junction Temperature**



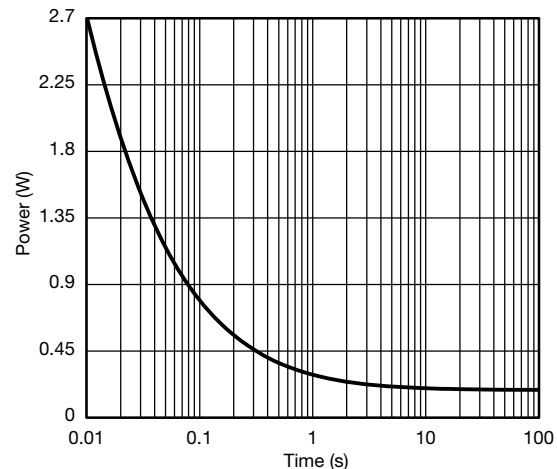
**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



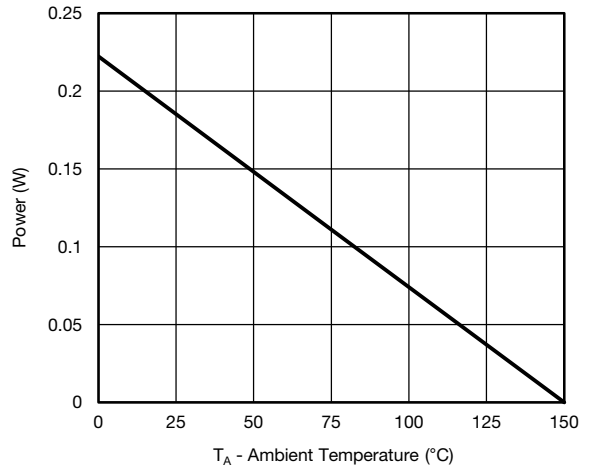
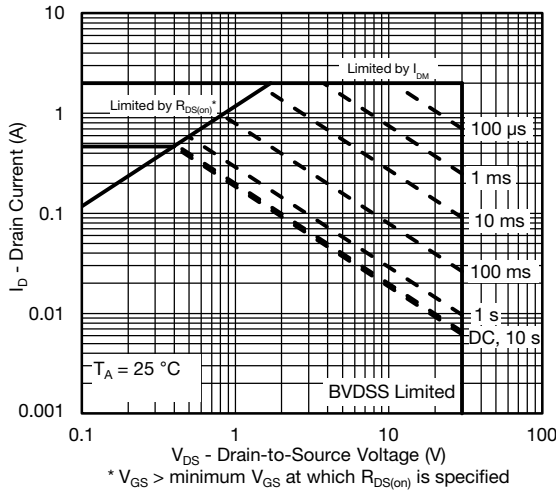
**Threshold Voltage**



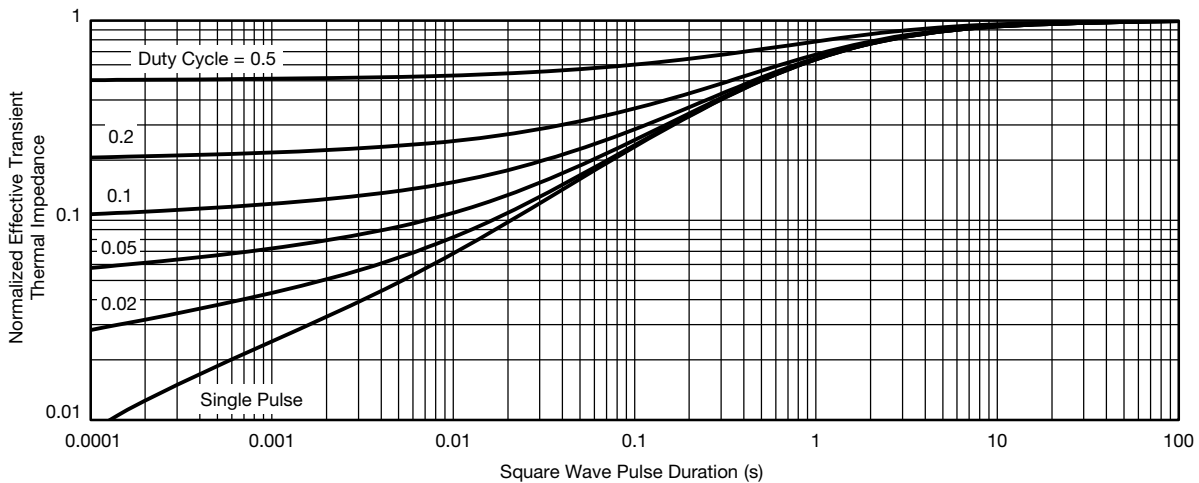
**Single Pulse Power, Junction-to-Ambient**



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

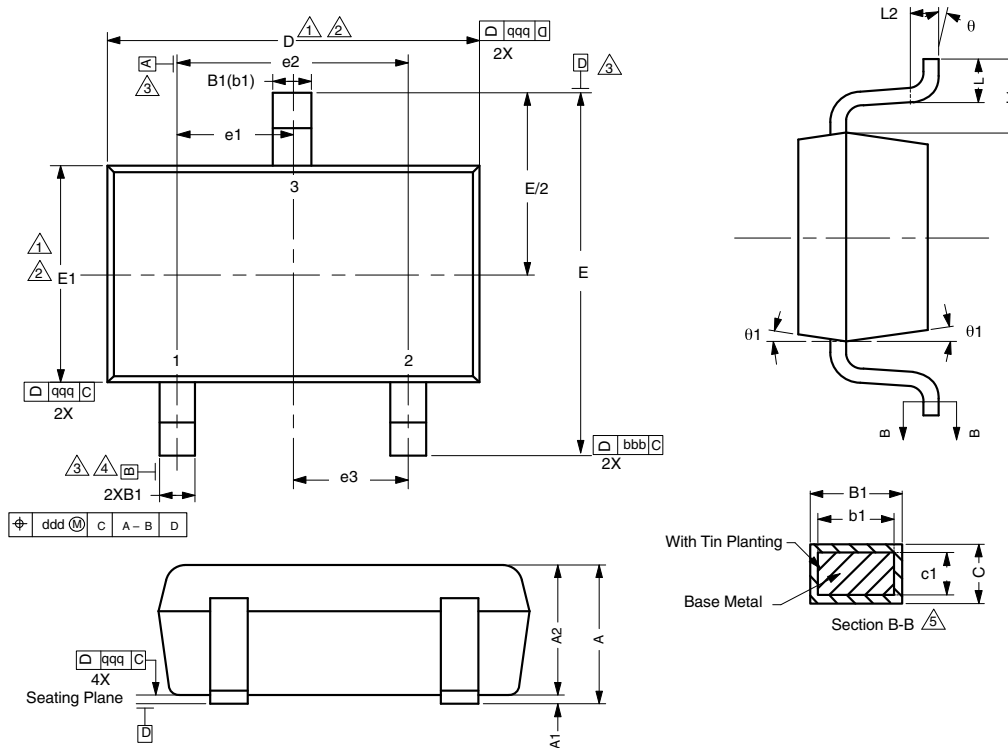


\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150\text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



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### SC-75A: 3 Leads



DWG: 5868

**Notes**

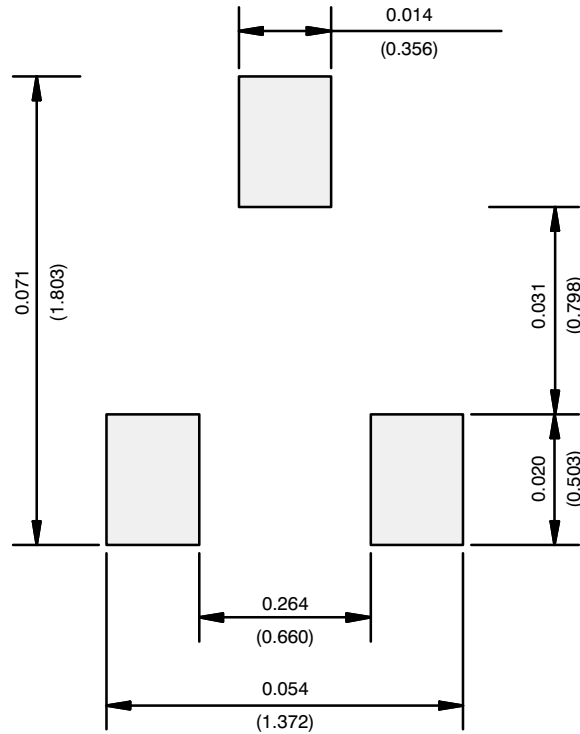
Dimensions in millimeters will govern.

- 1. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
- 2. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
- 3. Datums A, B and D to be determined 0.10 mm from the lead tip.
- 4. Terminal positions are shown for reference only.
- 5. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIMENSIONS	TOLERANCES
aaa	0.10
bbb	0.10
ccc	0.10
ddd	0.10

DIM.	MILLIMETERS			NOTE
	MIN.	NOM.	MAX.	
A	-	-	0.80	
A1	0.00	-	0.10	
A2	0.65	0.70	0.80	
B1	0.19	-	0.24	5
b1	0.17	-	0.21	
c	0.13	-	0.15	5
c1	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
E	1.50	1.60	1.70	
E1	0.66	0.76	0.86	1, 2
e1	0.50 BSC			
e2	1.00 BSC			
e3	0.50 BSC			
L	0.15	0.205	0.30	
L1	0.40 ref.			
L2	0.15 BSC			
q	0°	-	8°	
q1	4°	-	10°	

RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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